

IN THE CLAIMS:

Please amend Claims 1 and 3 to 6 as shown below. The claims, as pending in the subject application, read as follows:

1. (Currently Amended) A liquid phase growth method comprising the steps of:

immersing a substrate in a crucible that stores a solvent having a growth material dissolved therein; and

flowing a medium through a medium flow path provided in the solvent, without blowing the medium up through the solvent, to cool ~~cooling~~ the solvent from an interior thereof.

2. (Original) The liquid phase growth method according to Claim 1, wherein the solvent is cooled from a central part thereof.

3. (Currently Amended) The liquid phase growth method according to Claim 1, wherein the ~~cooling step is carried out by letting a medium flow through a tube~~ medium flow path comprises a tube through which the medium flows immersed in the crucible.

4. (Currently Amended) The liquid phase growth method according to Claim 1, wherein the ~~cooling step is carried out by letting a medium flow through a hole~~

medium flow path comprises a tube through which the medium flows formed in a jig for holding the substrate.

5. (Currently Amended) The liquid phase growth method according to Claim 1, wherein the ~~cooling step is carried out by letting a medium flow through a hole~~ medium flow path comprises a hole through which the medium flows formed in the crucible.

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cont'd*

6. (Original) The liquid phase growth method according to Claim 3, wherein the medium is a gas.

7. (Original) The liquid phase growth method according to Claim 1, wherein a liquid phase growth bath for formation of a p⁻ type Si layer is used as the crucible and, subsequent thereto, a liquid phase growth bath for formation of an n⁺ type Si layer is used as the crucible.

8. (Original) The liquid phase growth method according to Claim 1, wherein the growth material is Si, Ge, or GaAs.

9. (Original) The liquid phase growth method according to Claim 1, wherein the solvent is a melt of In or Sn.

10. (Withdrawn) A liquid phase growth apparatus comprising:

a crucible for storing a solvent having a growth material dissolved therein;
a wafer cassette for holding a substrate to be immersed in the solvent; and
a cooling section for cooling the solvent from an interior thereof.

11. (Withdrawn) The liquid phase growth apparatus according to Claim 10,
wherein the cooling section is a tube which is immersed in the crucible and through which
a medium is made to flow.

12. (Withdrawn) The liquid phase growth apparatus according to Claim 10,
wherein the cooling section is a hole which is formed inside the wafer cassette and through
which a medium is made to flow.

13. (Withdrawn) The liquid phase growth apparatus according to Claim 10,
wherein the cooling section is a hole which is formed in the crucible and through which a
medium is made to flow.

14. (Withdrawn) The liquid phase growth apparatus according to Claim 11,
wherein the medium is a gas.

15. (Withdrawn) The liquid phase growth apparatus according to Claim 14,
wherein the gas is hydrogen or nitrogen gas as an atmospheric gas.

16. (Withdrawn) The liquid phase growth apparatus according to Claim 10,

wherein the crucible comprises a liquid phase growth bath for formation of a p⁺ type Si layer and a liquid phase growth bath for formation of an n⁺ type Si layer.

17. (Withdrawn) The liquid phase growth apparatus according to Claim 10, wherein the wafer cassette is rotatable about its own axis.

18. (Withdrawn) The liquid phase growth apparatus according to Claim 10, wherein the wafer cassette is revolvable about an axis different from its own axis.

19. (Withdrawn) The liquid phase growth apparatus according to Claim 10, wherein the growth material is Si, Ge, or GaAs.

20. (Withdrawn) The liquid phase growth apparatus according to Claim 10, wherein the solvent is a melt of In or Sn.